MOSFETs Silicon N-Channel MOS

SSM3K376R

1. Applications

- Power Management Switches
- DC-DC Converters

2. Features

(1) AEC-Q101 qualified (Please see the orderable part number list)

(2) 1.8-V gate drive voltage.

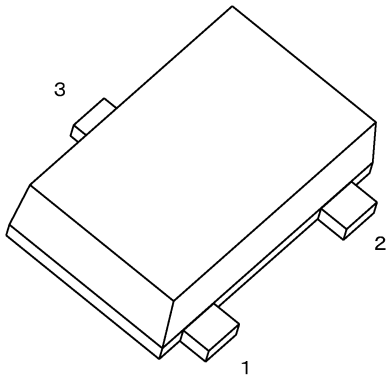
(3) Low drain-source on-resistance

: $R_{DS(ON)}$ = 56 mΩ (max) (@V_{GS} = 4.5 V)

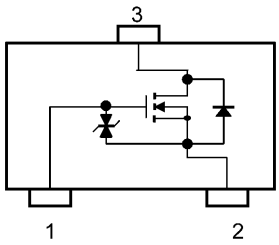
$R_{DS(ON)}$ = 72 mΩ (max) (@V_{GS} = 2.5 V)

$R_{DS(ON)}$ = 109 mΩ (max) (@V_{GS} = 1.8 V)

3. Packaging and Pin Assignment



SOT-23F



1: Gate
2: Source
3: Drain

4. Orderable part number

Orderable part number	AEC-Q101	Note
SSM3K376R,LF	—	General Use
SSM3K376R,LXGF	YES (Note 1)	Unintended Use (Note 1)
SSM3K376R,LXHF	YES	Automotive Use

Note 1: For more information, please contact our sales or use the inquiry form on our website.

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5. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	30	V
Gate-source voltage			V_{GSS}	12/-8	
Drain current (DC)		(Note 1)	I_D	4	A
Drain current (pulsed)		(Note 1), (Note 2)	I_{DP}	10	
Power dissipation		(Note 3)	P_D	1	W
Power dissipation	(t ≤ 10 s)	(Note 3)	P_D	2	
Channel temperature			T_{ch}	150	°C
Storage temperature			T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Pulse width (PW) ≤ 10 ms, duty ≤ 1%

Note 3: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm ,Cu pad: 645 mm^2)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, $R_{th(ch-a)}$, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

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6. Electrical Characteristics

6.1. Static Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{DS} = 0 V, V_{GS} = 10/-8 V	—	—	±10	μA
Drain cut-off current		I_{DSS}	V_{DS} = 24 V, V_{GS} = 0 V	—	—	1	
Drain-source breakdown voltage		$V_{(BR)DSS}$	I_D = 1 mA, V_{GS} = 0 V	30	—	—	V
Drain-source breakdown voltage	(Note 1)	$V_{(BR)DSX}$	I_D = 1 mA, V_{GS} = -8 V	18	—	—	
Gate threshold voltage	(Note 2)	V_{th}	V_{DS} = 3 V, I_D = 1 mA	0.40	—	1.00	
Drain-source on-resistance	(Note 3)	$R_{DS(ON)}$	I_D = 2.0 A, V_{GS} = 4.5 V	—	45	56	mΩ
			I_D = 1.0 A, V_{GS} = 2.5 V	—	55	72	
			I_D = 0.5 A, V_{GS} = 1.8 V	—	69	109	
Forward transfer admittance	(Note 3)	$\|Y_{fs}\|$	V_{DS} = 3 V, I_D = 2 A	—	10.5	—	S

Note 1: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th}, and $V_{GS(OFF)}$ must be lower than V_{th}. This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.
Take this into consideration when using the device.

Note 3: Pulse measurement.

6.2. Dynamic Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	V_{DS} = 10 V , V_{GS} = 0 V, f = 1 MHz	—	200	—	pF
Reverse transfer capacitance	C_{rss}		—	13	—	
Output capacitance	C_{oss}		—	40	—	
Switching time (turn-on time)	t_{on}	V_{DD} = 10 V, I_D = 2 A, V_{GS} = 0 to 2.5 V, R_G = 4.7 Ω	—	9	—	ns
Switching time (turn-off time)	t_{off}		—	9.5	—	

6.3. Switching Time Test Circuit

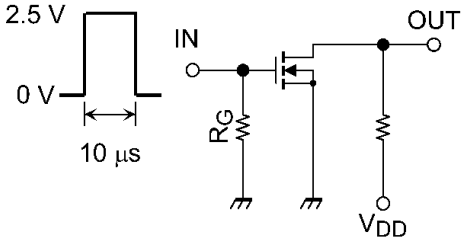


Fig. 6.3.1 Switching Time Test Circuit

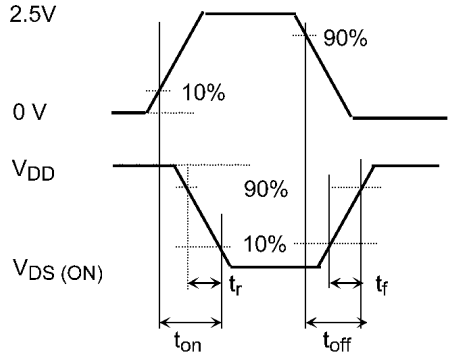


Fig. 6.3.2 Input Waveform/Output Waveform

6.4. Gate Charge Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V_{DD} = 10 V, I_D = 2.4 A, V_{GS} = 4.5 V	—	2.2	—	nC
Gate-source charge 1	Q_{gs1}		—	0.5	—	
Gate-drain charge	Q_{gd}		—	0.9	—	

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6.5. Source-Drain Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage (Note 1)	V_{DSF}	I_D = -4 A, V_{GS} = 0 V	—	-0.8	-1.2	V

Note 1: Pulse measurement.

7. Marking

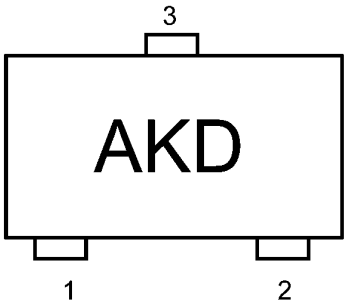


Fig. 7.1 Marking

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8. Characteristics Curves (Note)

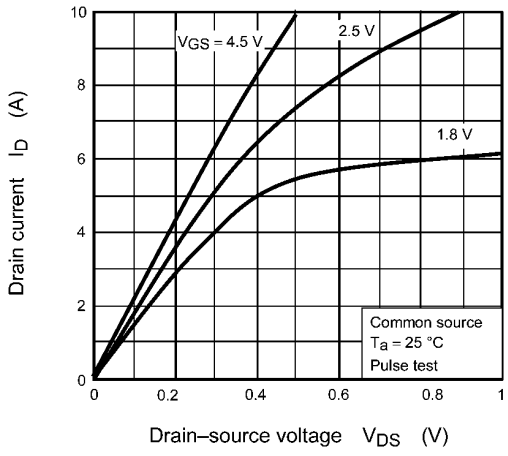


Fig. 8.1 I_D - V_{DS}

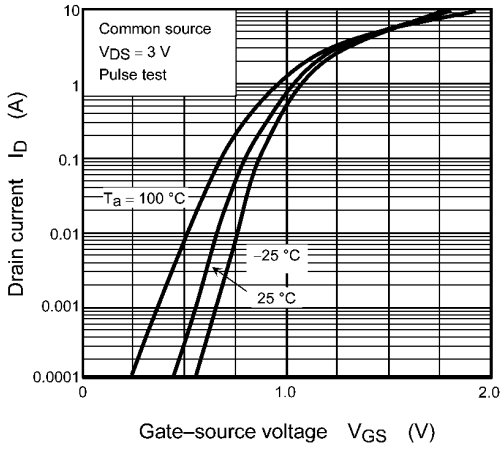


Fig. 8.2 I_D - V_{GS}

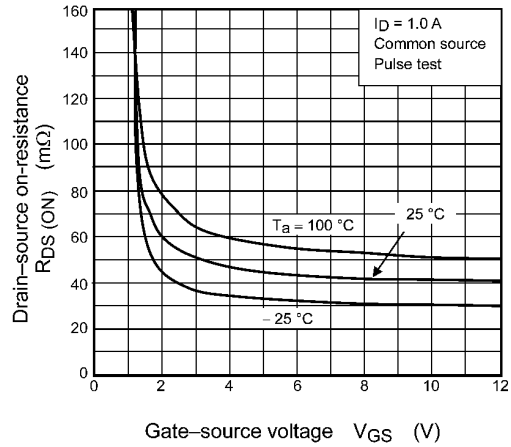


Fig. 8.3 $R_{DS(ON)}$ - V_{GS}

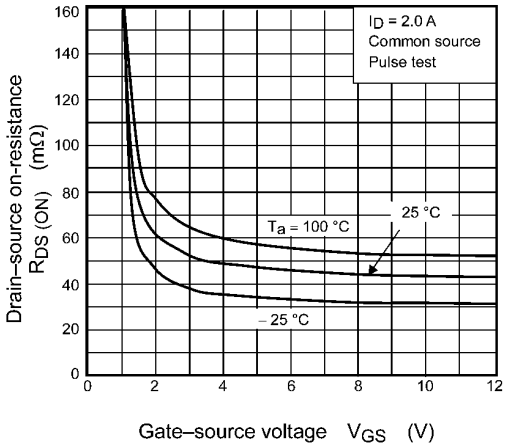


Fig. 8.4 $R_{DS(ON)}$ - V_{GS}

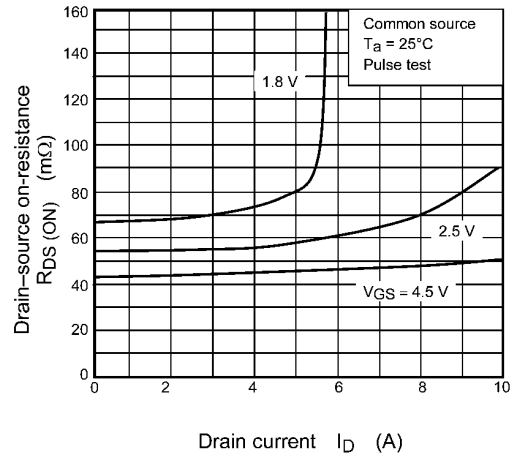


Fig. 8.5 $R_{DS(ON)}$ - I_D

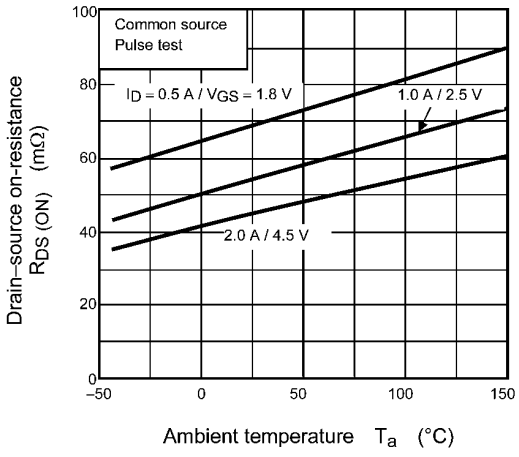


Fig. 8.6 $R_{DS(ON)}$ - T_a

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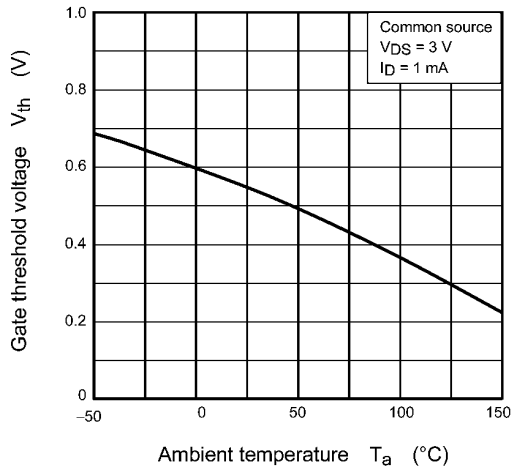


Fig. 8.7 V_{th} - T_a

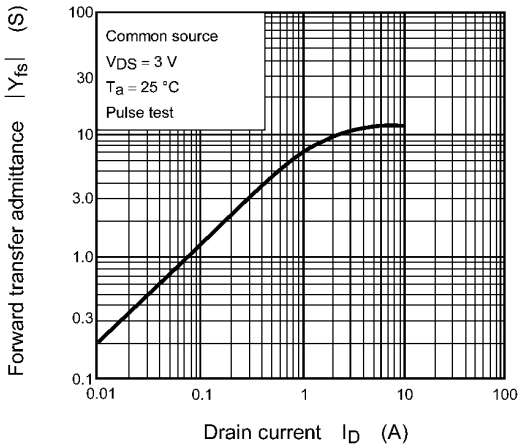


Fig. 8.8 $|Y_{fs}|$ - I_D

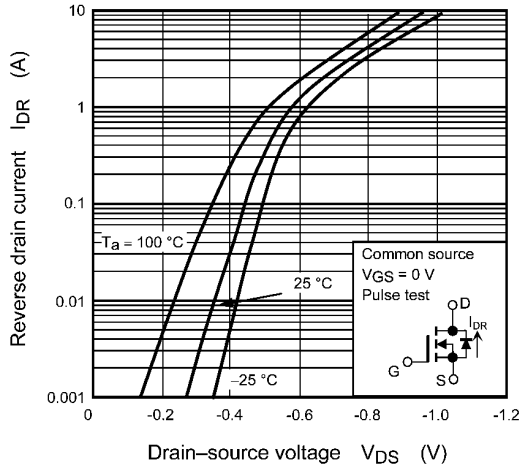


Fig. 8.9 I_{DR} - V_{DS}

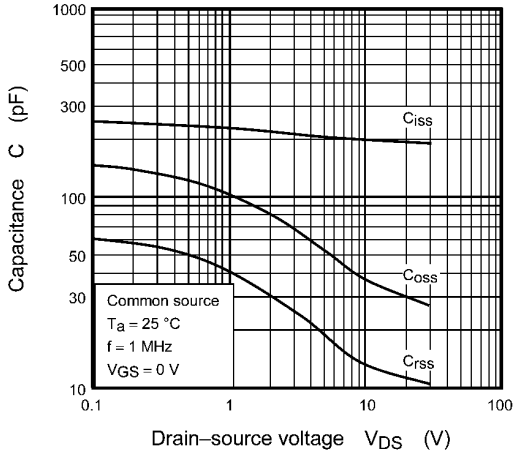


Fig. 8.10 C - V_{DS}

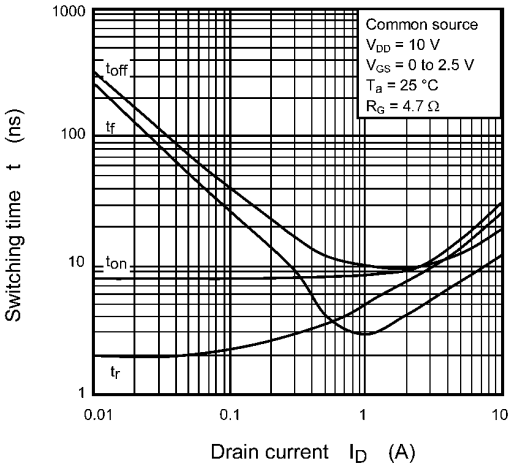


Fig. 8.11 t - I_D

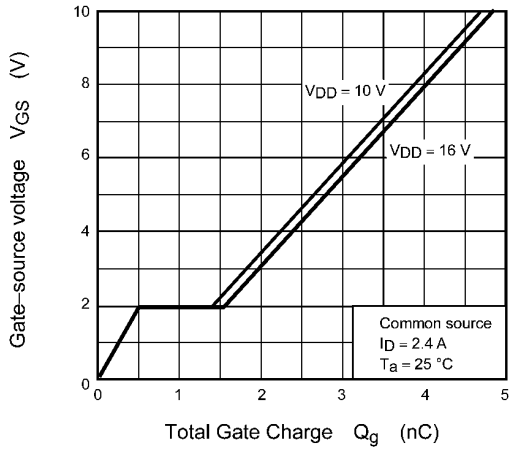


Fig. 8.12 Dynamic Input Characteristics

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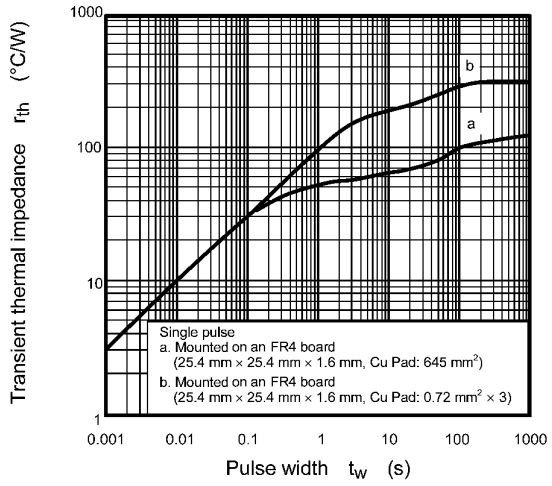


Fig. 8.13 r_{th} - t_w

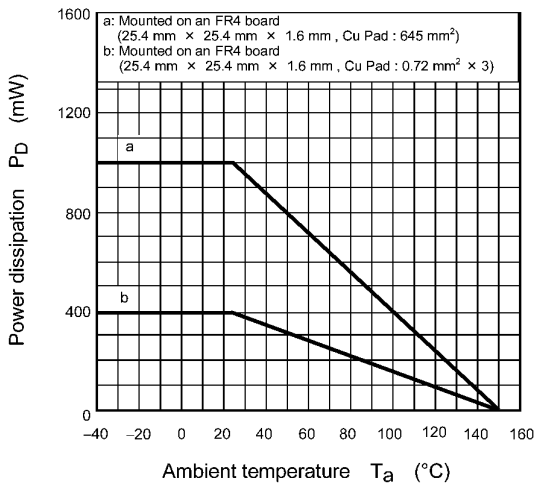


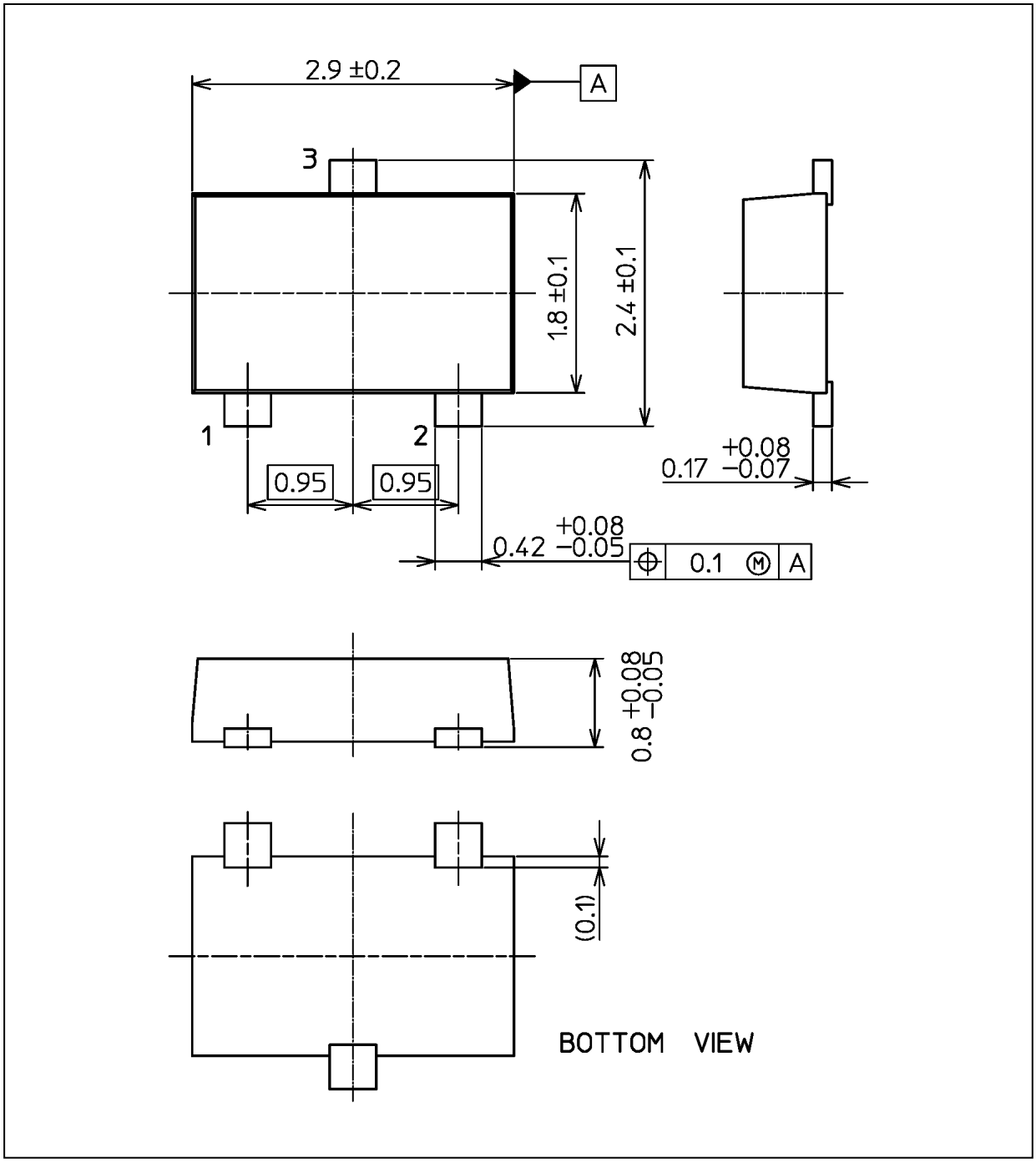
Fig. 8.14 P_D - T_a

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

Package Name(s)
Nickname: SOT-23F

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